

IN THE SPECIFICATION:

Please amend paragraph number [0013] as follows:

[0013] FIG. 1A is a side sectional view of a variant of the exemplary embodiment of FIG. 1A; FIG. 1;

Please amend paragraph number [0020] as follows:

[0020] An electrically insulative, or dielectric, material 110 may be disposed on active surface 104 to enable physical attachment of semiconductor die 100 by its active surface 104 to a second semiconductor substrate component in the form of another substrate. The dielectric material 110 may be disposed over the entire active surface 104, except for a small area surrounding each of the bond pads 102, defining a cavity 106 over each bond pad 102. The dielectric material 110 may comprise a layer of material applied in a flowable state, such as a thermoset resin in, for example, the form of an epoxy, or it may be screen printed or stenciled to define cavities 106 as it is applied and optionally cured to a tacky state, or so-called "B-stage." As with other semiconductor die fabrication processes, it is contemplated that such application would be effected to a semiconductor wafer, prior to singulation of semiconductor dice therefrom. Another approach is to spin coat a wafer with, for example, a polymer such as a polyimide, and then etch through the coating to expose bond pads 102. Further, dielectric material 110 may be applied to active surface 104 as a preformed film of, for example, polyimide (e.g., KAPTON® film), having apertures preformed therein and coated on both sides with a suitable adhesive. As yet another approach, a film of thermoplastic resin may be employed.